

WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:
a first conductive layer formed on a substrate;
an insulating interlayer positioned over the first conductive layer, the insulating interlayer having a contact hole that is at least partially disposed directly on the first conductive layer; and
a second conductive layer formed on the insulating interlayer, the second conductive layer being electrically coupled to the first conductive layer through the contact hole;
the contact hole extending beyond either an edge of the first conductive layer or an edge of the second conductive layer in plan view.
2. The semiconductor device according to claim 1, one of the first conductive layer and said second conductive layer entirely overlapping the contact hole and the other conductive layer partially overlapping the contact hole in plan view.
3. The semiconductor device according to claim 2, said one of the conductive layers being the first conductive layer and said other conductive layer being the second conductive layer.
4. The semiconductor device according to claim 2, a plurality of said other conductive layers extending parallel to one another at a predetermined pitch.
5. The semiconductor device according to claim 4, said one of the conductive layers intersecting said other conductive layer.
6. The semiconductor device according to one of claim 2, said other conductive layer overlapping the contact hole that is shifted to one side of said other conductive layer.
7. The semiconductor device according to claim 2, said other conductive layer overlapping the contact hole, two opposing edges of the contact hole being outside of said other conductive layer.
8. The semiconductor device according to claim 2, the contact hole being rectangular in plan view and the other conductive layer partially overlapping the contact hole in a lengthwise direction.
9. The semiconductor device according to claim 2, the contact hole being rectangular in plan view and the other conductive layer extending diagonally with respect to edges of the contact hole.

10. An electro-optical unit, the semiconductor device according to claim 1 being used for a substrate of the electro-optical unit to hold an electro-optical substance and pixels having pixel switching transistors, and pixel electrodes being disposed in a matrix on the substrate of the electro-optical unit.

11. The electro-optical unit according to claim 10, the electro-optical substance being liquid crystal disposed between the substrate of the electro-optical unit and a counter substrate.

12. The electro-optical unit according to claim 10, the electro-optical substance being an organic electroluminescent substance that constitutes light emitting elements on the substrate of the electro-optical unit.

13. An electronic apparatus comprising the electro-optical unit according to claim 10.